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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.: 09/519,165
Filing Date: March 6, 2000
Inventors: David W. Sherrer et al.
Title: Single Mask Lithographic
Process For Patterning
Multiple Types Of Surface
Features

BOX RCE

Examiner: W. Watkins, III

Art Unit: 1772

Assistant Commissioner for Patents
Washington, DC 20231

FAX RECEIVED
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GROUP 1700AMENDMENT

Sir:

In response to the final Official Action issued September 25, 2002, applicants submit the following amendments and remarks:

IN THE CLAIMS:

Please amend the claims as follows:

1. (Amended) A method for fabricating the etched optoelectronic apparatus of claim 1, comprising the steps of:
- a) providing a semiconductor substrate with a top surface and a planar dielectric layer on the top surface;
 - b) forming a patterned metal layer on the dielectric layer, wherein the patterned metal layer has a metal edge;
 - c) forming a patterned resist layer on the dielectric layer and patterned metal layer, wherein the resist layer has a resist edge that is located on top of the metal layer such that the dielectric layer has an exposed area defined by the metal edge;
 - d) etching away the dielectric layer from the exposed area;
 - e) etching the semiconductor substrate where the dielectric layer is etched away in step (d), thereby forming a pit; and
 - f) placing an optical element into the pit.